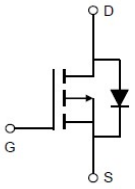
-60V P-Channel Power MOSFET

• General Description

It combines trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Product Summary



V_{DS}= -60V

$R_{DS(ON)}$ = 103mΩ

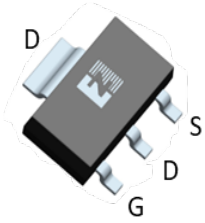
I_D= -2.8A

• Features

■Low $R_{DS(ON)}$ to minimize conductive loss

■High GOX reliability

■Low Thermal resistance



SOT-223

•Application

■BLDC Motor driver

■DC-DC

■Load Switch

•Ordering Information:

Part NO.	ZM930P06E
Marking	930P06
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

•Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		-60	V
Gate-Source Voltage	V_{GS}		±20	V
Continuous Drain Current	I_D	T_C=25℃	-2.8	A
	I_D	T_C=75℃	-2.8	A
	I_D	T_C=100℃	-2.7	A
Pulsed Drain Current	I_{DM}	Pulsed; t_p ≤ 10 μs; T_{mb} = 25 °C;	-11.2	A
Total Power Dissipation	P_D	T_C=25℃	5	W
Total Power Dissipation	P_D	T_A=25℃	1.8	W
Operating Junction Temperature	T_J		-55 to +150	℃
Storage Temperature	T_{STG}		-55 to +150	℃
Single Pulse Avalanche Energy	E_{AS}	L=0.1mH, V_{GS}=-10V, Rg=25Ω,	1.2	mJ
		L=0.5mH, V_{GS}=-10V, Rg=25Ω,	2.52	mJ
ESD Level (HBM)	CLASS 2			

●Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	25	°C/W
Thermal resistance, junction-ambient①	R_{thJA}		-	70	°C/W
Soldering temperature	Tsold		-	260	°C

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V, I_D =-250uA	-60			V
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} =V_{DS}, I_D =-250uA	-1.3	-1.8	-2.5	V
Drain-Source Leakage Current	I_{DSS}	V_{GS}=0V, V_{DS}= -60V			1.0	uA
Gate- Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS} = 0V			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D= -1.5A		103	130	mΩ
		V_{GS}=-4.5V, I_D= -1A		128	166	mΩ
Forward Transconductance	g_{FS}	V_{DS} =-5V, I_{SD} = -1A		20		S
Diode Forward Voltage	V_{FSD}	V_{GS} =0V, I_{SD} = -1.5A			1.3	V

●Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	Ciss	f = 1MHz, V_{DS}=-25V	-	650	-	pF
Output capacitance	Coss		-	95	-	
Reverse transfer capacitance	Crss		-	70	-	
Gate Risistance	Rg	f = 1MHz	-	8		Ω
Total gate charge	Qg	V_{DD} = -15V, I_D = -1.5A, V_{GS} = -10V	-	12	-	nC
	Qg(-4.5v)		-	21	-	
Gate - Source charge	Qgs		-	1.6	-	
Gate - Drain charge	Qgd		-	2.6	-	
Turn-ON Delay time	$t_{D(on)}$	V_{GS}=-10V,V_{DS}=-15V, R_G =3.3Ω, I_D =-1A	-	6.5	-	ns
Turn-ON Rise time	t_r		-	8	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	16.5	-	ns
Turn-Off Fall time	t_f		-	4	-	ns

Fig.1 Gate-Charge Characteristics

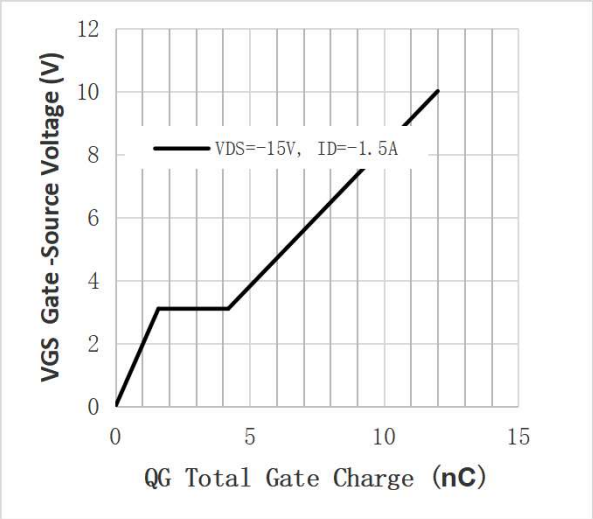


Fig.2 Capacitance Characteristics

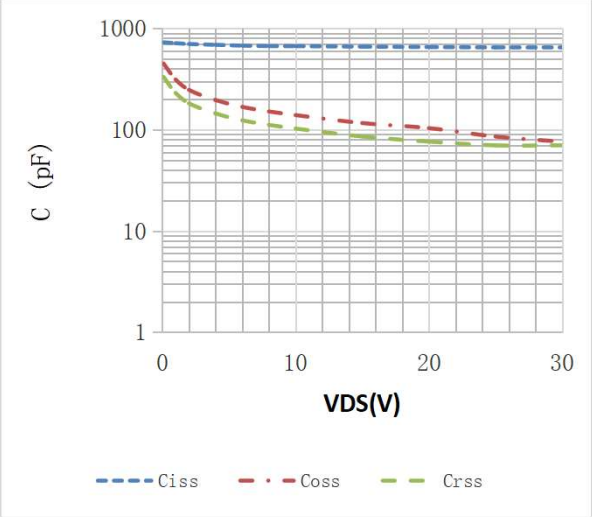


Fig.3 Power Dissipation

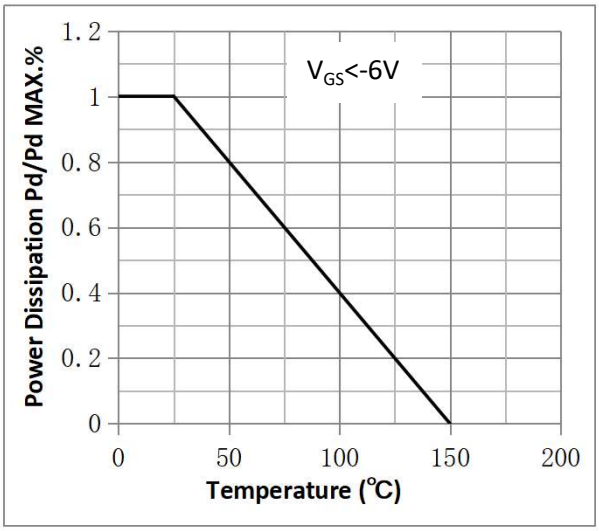


Fig.4 Typical output Characteristics

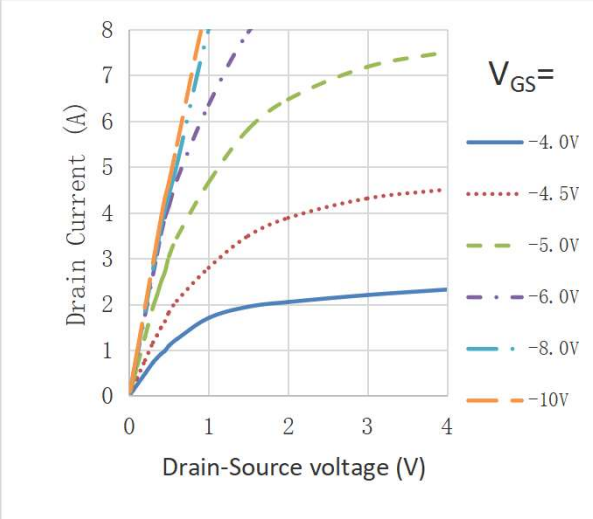


Fig.5 Threshold Voltage V.S Junction Temperature

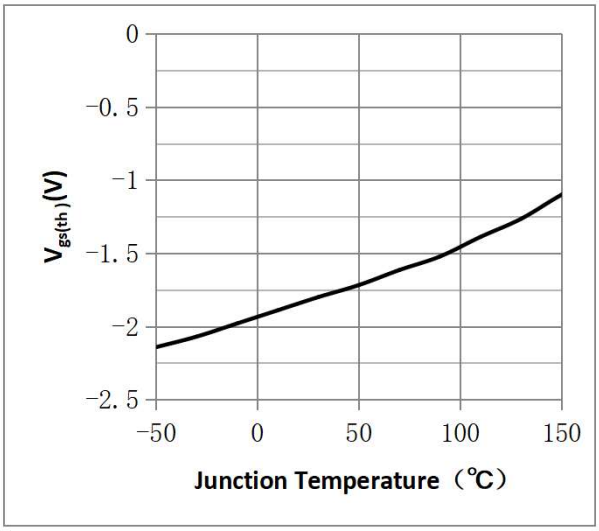


Fig.6 Resistance V.S Drain Current

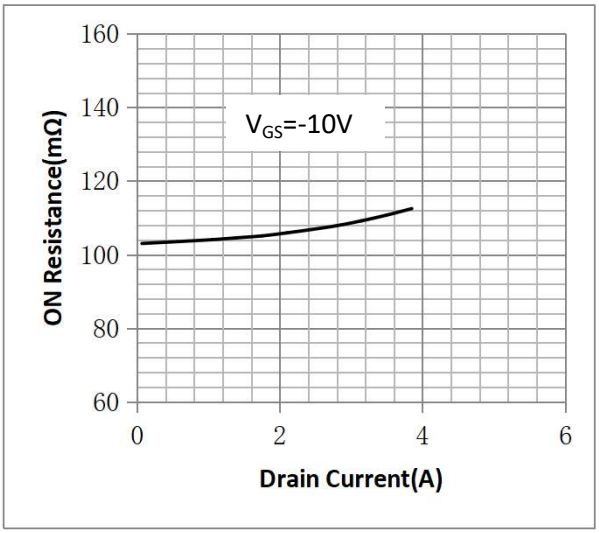


Fig.7 On-Resistance VS Gate Source Voltage

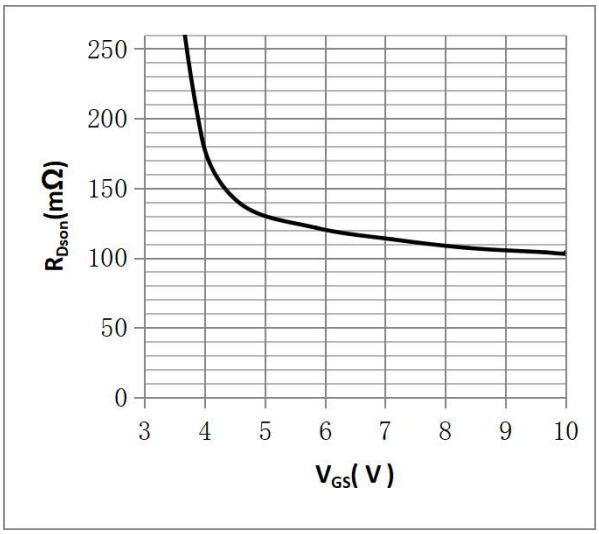


Fig.8 On-Resistance V.S Junction Temperature

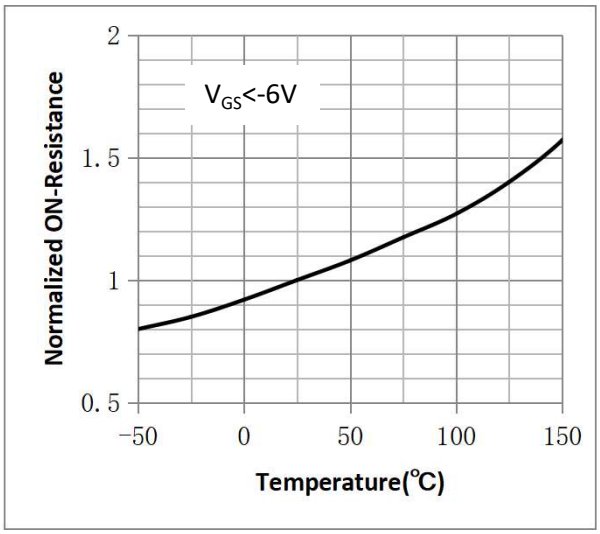


Figure 9. Diode Forward Voltage vs. Current

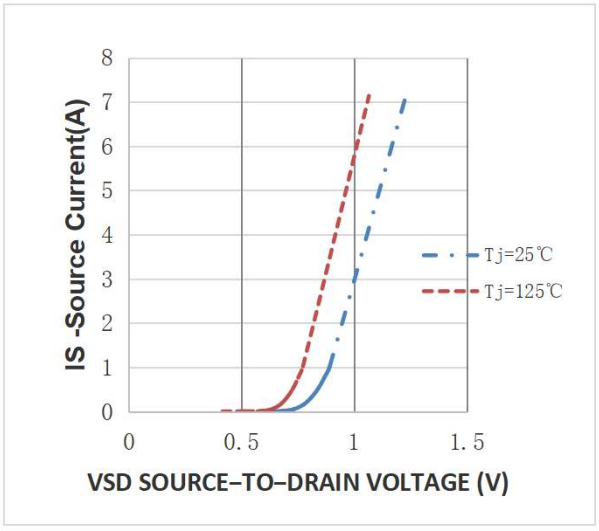


Figure 10. Transfer Characteristics

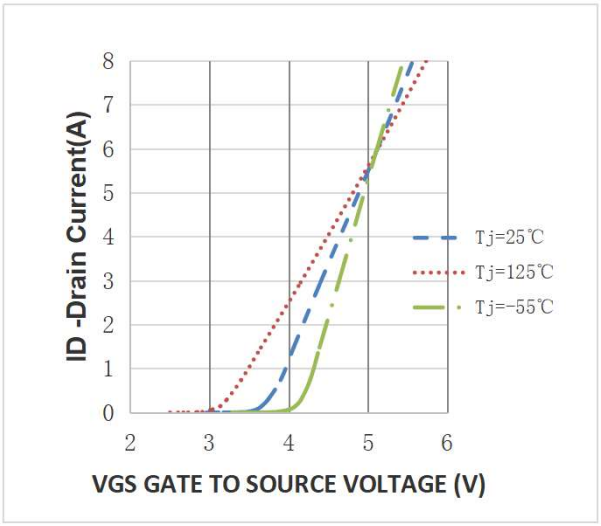


Fig.11 Safe Operating Area

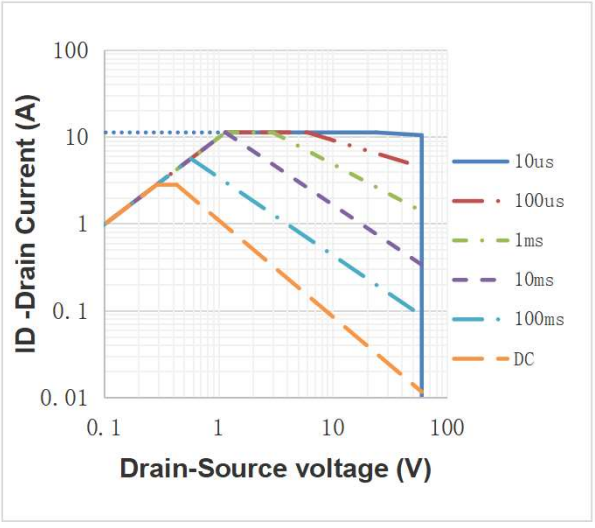
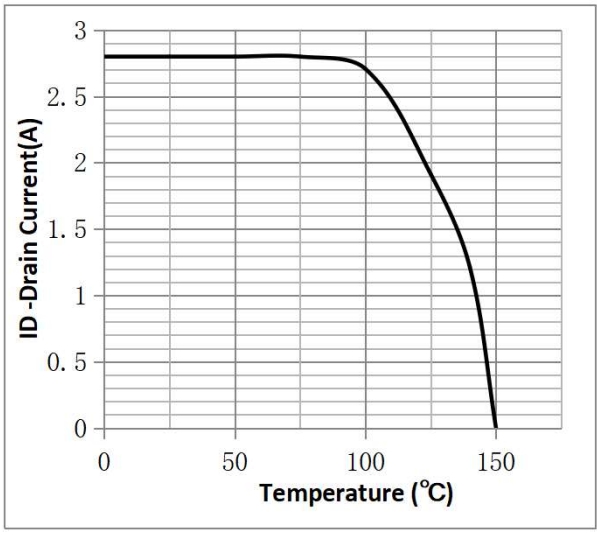
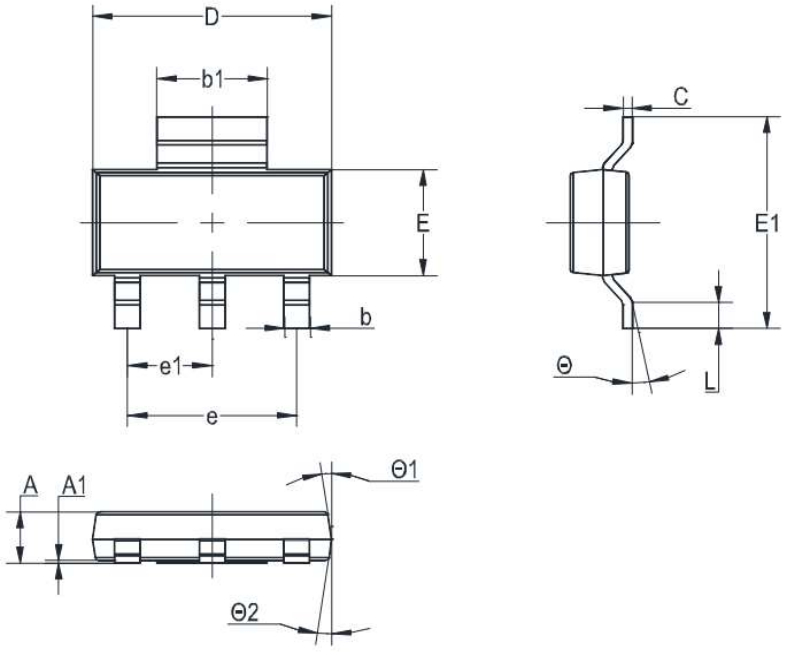


Fig.12 ID vs. Case Temperature②

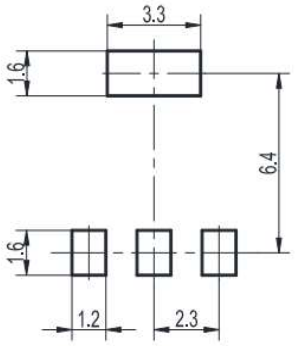


●SOT-223 Package Outline



Unit	A	A1	b	b1	C	D	E	E1	e	e1	L	Θ	Θ1	Θ2
mm	1.8 1.5	0.1 MAX	0.8 0.6	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	7.3 6.7	4.6 TYP	2.3 TYP	1.1 0.7	10° 0°	7° 0°	7° 0°

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-223	12	8 ± 0.1	0.315 ± 0.004	330	13	3,000

Note:

① Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate；

②Practically the current will be limited by PCB, thermal design and operating temperature. VGS=-10V.

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Revision History

Version	Date	Change
A	2021.11.3	NEW
B	2022.5.7	1.Add Reach,HF figure